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PL IMAGE OF AS-GROWN DEFECTS IN CZ Si
SCAN AREA 1mm x 1mm

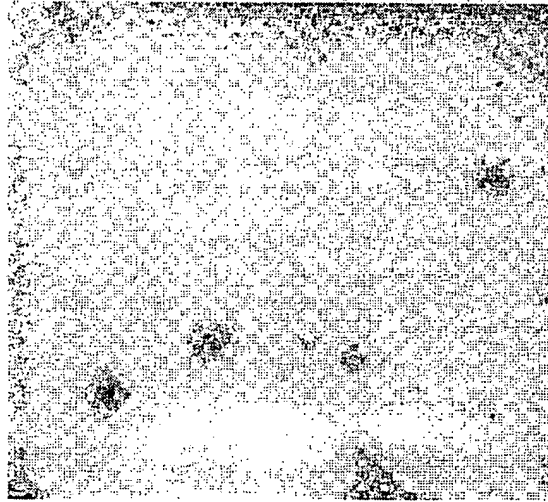


Fig. 1

PL IMAGE OF AS-GROWN DEFECTS IN CZ Si AFTER Fe CONTAMINATION 1×10^{11} atoms.cm⁻³
SCAN AREA 1mm x 1mm

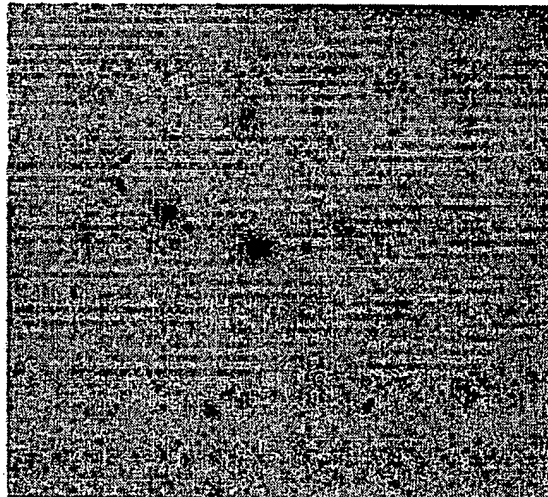


Fig. 2

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PL IMAGE OF OXYGEN PRECIPITATES IN ANNEALED Si
SCAN AREA 1mm x 1mm

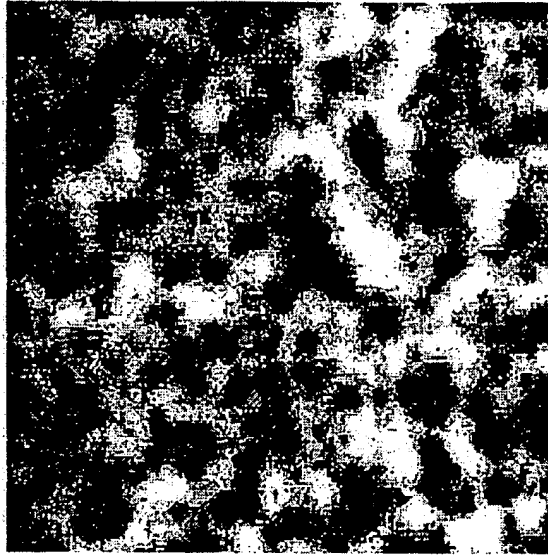


Fig. 3

PL IMAGE OF Ni SILICIDE PRECIPITATES IN CMOS PROCESSED TEST WAFER
SCAN AREA 500 x 500 μm

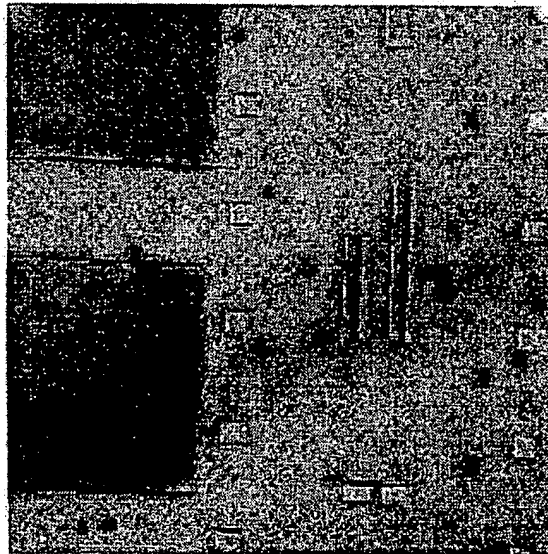


Fig. 4

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PL IMAGE OF Cu SILICIDE PRECIPITATES IN CMOS PROCESSED TEST WAFER
SCAN AREA 100mm x 100 μ m

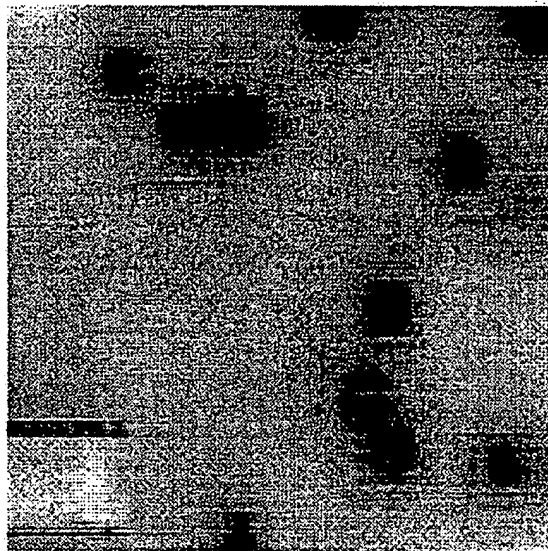
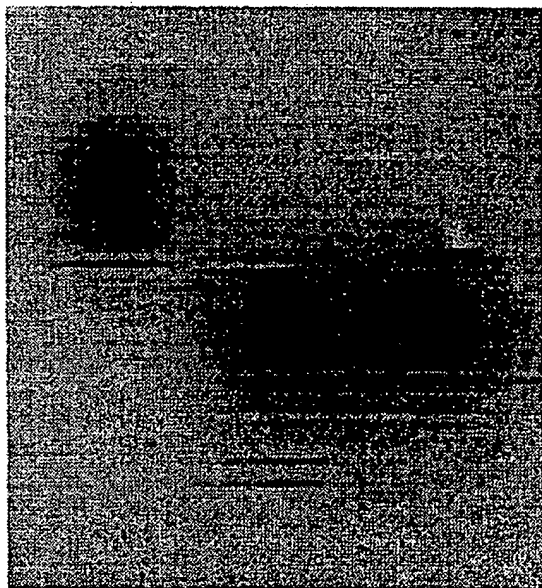


Fig. 5

PL IMAGE OF Cu SILICIDE PRECIPITATES IN CMOS PROCESSED TEST WAFER,
a) HIGH INJECTION, b) LOW INJECTION.
SCAN AREA 37 x 39 μ m

a)



b)

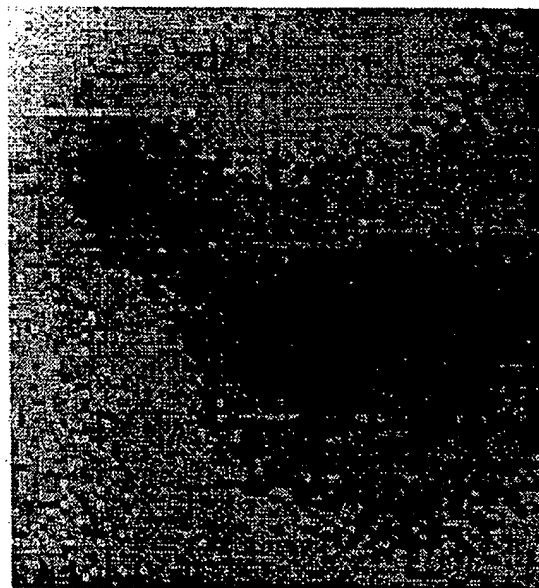


Fig. 6

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MICROGRAPH OF LOCOS TEST STRUCTURE
SCAN AREA 120 x 60 μm

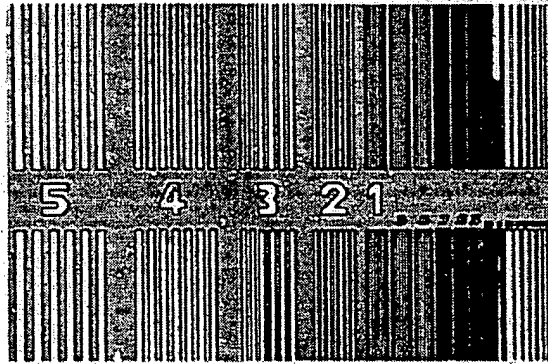


Fig. 7

PL IMAGE OF LOCOS TEST STRUCTURE REVEALING A HIGH DENSITY OF DISLOCATIONS
SCAN AREA 120 x 60 μm

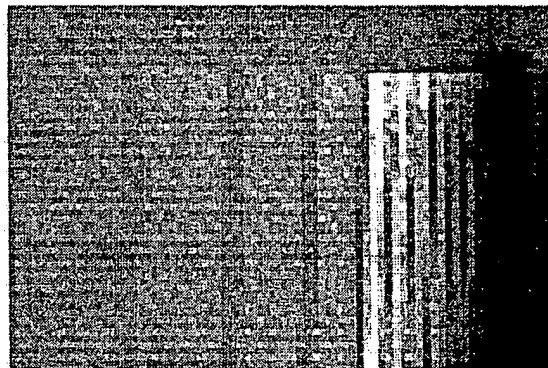


Fig. 8

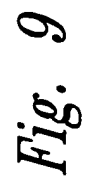


Fig. 9